

## First/Second Semester B.E. Degree Examination, June/July 2013 Basic Electronics

Time: 3 hrs.	Max. Marks:100
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Note: 1. Answer any FIVE full questions, choosing at least two from each part.

- 2. Answer all objective type questions only in OMR sheet page 5 of the answer booklet.
- 3. Answer to objective type questions on sheets other than OMR will not be valued.

		<u>PART – A</u>		
1	a.	Choose the correct answers for the following:		(04 Marks)
		i) Forward cut-in voltage of Silicon diode is		
		A) 0.3 V B) 0.2 V	C) 0.6 V	D) 0.8 V
		ii) A Zener diode can be used as		
		A) regulator B) rectifier	C) amplifier	D) oscillator
		iii) The ripple factor of half wave rectifier is	A) 0.48 B) 0.64	
		iv) A semiconductor has temperature coeffici		,
		A) positive B) negative	C) neutral	D) none of these
	b.	Explain the V-I characteristics of a Silicon diode.		(04 Marks)
	c.	Explain the circuit of full wave rectifier and show that rip	ople factor is 0.48.	(06 Marks)
	d.	Design a Zener diode voltage regulator to meet the follow		(4.4.1.544.544.)
		DC input voltage $V_i = 20 \text{ V}$ ; DC output vo	$ltage V_0 = 10 V$ :	Load current $I_L = 20 \text{ mA}$ ;
		DC input voltage $V_i = 20 \text{ V}$ ; DC output vo Minimum Zener current $I_{zmin} = 10 \text{ mA}$ ; Maximum Ze	ner current $I_{max} = 100 \text{ m/s}$	(06 Marks)
			Zinax	(10.11.11.11.11.11.11.11.11.11.11.11.11.1
2	a.	Choose the correct answers for the following:		(04 Marks)
		i) A transistor has PN junctions. A) one	B) two C) three	
		ii) The value of ' $\alpha$ ' is equal toA) < 1	B) $> 1$ C) 1	D) zero
		iii) In the active region of CE amplifier the base emitter		2) 20.0
			C) forward biased	D) none of these
		iv) Common collector arrangement can be used for	application.	_,
		iv) Common collector arrangement can be used for A) high frequency B) audio frequency	C) impedance matchin	ng D) none of these
	b.	Explain the input, output and current gain characteristic	s of common base config	uration and also explain the
		concept of punch through.		(08 Marks)
	c.	Define Q-point and DC load line. For the circuit shown in	Fig.O2(c), draw DC load	
		Assume $\beta = 100$ , neglect $V_{BE}$ .	, * · · · · · · · · · · · · · · · · · ·	(08 Marks)
			· [	Vcc= 24V
		V <sub>cc</sub> =30V	II \$1	RC=8,3KV
		1.5Ma\$Rz \$Ri=5ks	180KD = RIS I.	
		Light SVB Syr-2005	1800	CE
			Ti TB	<i>)</i>
			~ ~ ~ ~ ~ ~ ~ ~ ~ ~ ~ ~ ~ ~ ~ ~ ~ ~ ~	ÎE
			56KD=R2} }	RE=4.7Kn
		· 7		
		· .	3	
		Fig.Q2(c)	Fig.Q3(	c)
		· <b>6</b> · <b>(</b> -(-)		
3	a.	Choose the correct answers for the following:		(04 Marks)
		i) The most commonly used transistor configuration is	circuit.	(01
		A) CB B) CC	C) CE	D) BC
		ii) The best method of transistor bias is	,	_,
		A) self bias B) feedback resistor	C) base resistor	D) none of these
		iii) Stabilization means making independent	of temperature variation	n or variation in transistor
		parameters.		· · · · · · · · · · · · · · · · ·
		A) knee point B) operating point	C) threshold point	D) none of these

State the need for biasing and explain different types of biasing with relevant diagrams and equations. (08 Marks) Determine  $I_C$ ,  $V_E$ ,  $V_C$  and  $V_{CE}$  for the circuit shown in Fig.Q3(c), and assume  $V_{BE} = 0.7 \text{ V}$ . (08 Marks)

C) faithful amplification D) punch through

B) unfaithful amplification

iv) If the operating point changes it results in

A) thermal runway

4	a.		Marks)
		i) FET is controlled device. A) current B) voltage C) bandwidth D) power	r
		ii) UJT has junctions. A) one B) two C) three D) four	
		iii) The anode of the SCR is always maintained at potential with respect to cathode.	
		A) zero B) negative C) positive D) none of these	ę
		iv) JFET is transistor.	
		A) bipolar B) unipolar C) tripolar D) none of these	;
	b.		Marks)
	c.		Marks)
	d.	in the second of	Marks)
		· · · · · · · · · · · · · · · · · · ·	•
		<u>PART – B</u>	
5	a.		Marks)
•	u.	i) The input and output voltages of single stage CE transistor amplifier are out of phase.	,
		A) 360° B) 90° C) 180° D) 45°	
		ii) The negative voltage feedback the gain of an amplifier.	
		A) decreases B) increases C) remains same as D) none	
		iii) In phase shift oscillator, generally RC stages are used.	
		A) one B) two C) three D) four iv) Oscillator employs feedback.	
		iv) Oscillator employs reedback.	
		A) negative B) positive C) both +ve and -ve D) none of these	
	b.		Marks)
	c.		Marks)
	d.	In RC phase shift oscillator R = $5 \text{ k}\Omega$ and C = $0.1 \mu\text{F}$ . Calculate frequency of oscillation. (02)	Marks)
6	a.	Choose the correct answers for the following:	Marks)
		i) The CMRR of an ideal OP-AMP is A) finite B) infinite C) zero D) none of	these
		ii) Slew rate of an OPAMP is given by A) $\frac{dl_o}{dt}$ B) $\frac{dV_o}{dl_o}$ C) $\frac{dV_o}{dt}$ D) $\frac{dl_o}{dV_o}$	
		II) Slew rate of an OPAMP is given by A) $\frac{1}{dt}$ B) $\frac{1}{dt}$ C) $\frac{1}{dt}$ D) $\frac{1}{dt}$	
		at ar <sub>o</sub> at av <sub>o</sub>	
		iii) An ideal OP-AMP characteristics do not change with  A) pressure B) power C) frequency D) temperature iv) The heart of CRO is A) CRT B) electron gun C) deflecting plates D) screen	
		A) pressure B) power C) frequency D) temperature	
		iv) The heart of CRO is A) CRT B) electron gun C) deflecting plates D) screen	
	b.	List the ideal characteristics of an OP-AMP. (04	Marks)
	c.	Draw the circuit of OPAMP as summer and derive an expression for output voltage.	Marks)
	d.	Explain the block diagram of CRO.	Marks)
7	a.	Choose the correct answers for the following:	Marks)
		i) If m = 1, the sidebands carry % of AM wave power.	
		A) 33.3 B) 46.6 C) 81.1 D) 95.5 ii) $(110101)_2 = (?)_{10}$ A) $(34)_{10}$ B) $(64)_{10}$ C) $(90)_{10}$ D) $(53)_{10}$	
		ii) $(110101)_2 = (?)_{10}$ A) $(34)_{10}$ B) $(64)_{10}$ C) $(90)_{10}$ D) $(53)_{10}$	
		iii) $(283)_{10} = (?)_8$ A) $(324)_8$ B) $(433)_8$ C) $(456)_8$ D) $(402)_8$	
		iv) 2's complement of binary number 1011 is A) 1100 B) 0101 C) 0110 D) 101	0
	b.	Derive an expression for the instantaneous value of an AM signal in terms of carrier and sideband frequency	
	•	·	Marks)
	c.	A 15 kHz audio signal is used to frequency modulate a 100 MHz carrier causing a carrier deviation of 1	75 kHz.
		Determine modulation index. (02	Marks)
	đ.	i) Convert $(1024.625)_{10} = (?)_2$ ii) Convert $(ABCD)_{16} = (?)_2 = (?)_8$	
			Marks)
			•
8	a.		Marks)
		i) Absorption property states that $A + \overline{AB} = \underline{\hspace{1cm}}$ . A) $\overline{A} + \overline{B}$ B) $\overline{B} + \overline{A}$ C) A D) A	+ B
		<del></del>	
		ii) Idempotent property states that $A.A = $ $A) A$ $B) I$ $C) 0$ $D) A$	
		iii) AB + ABC + ABD = A) ABC B) A + B C) AB D) A + D	
		iv) The output is high, when all the inputs are high, such gate is called	
		A) NOT gate B) AND gate C) NAND gate D) NOR gate	
	b.	A DO A DO A DO A DA A O	Market
			Marks)
	c.		Marks)
	d.	Simplify the following expression and implement using NAND gates only.	
		$A = (A + (\overline{BC})(\overline{A} + B + \overline{C})(A + \overline{B})$	Marks)

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